

Features

- Low $R_{DS(ON)}$:
 - 80 m Ω @ $V_{GS} = -4.5V$
 - 110 m Ω @ $V_{GS} = -2.7V$
 - 130 m Ω @ $V_{GS} = -2.5V$
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 3)**
- Qualified to AEC-Q101 Standards for High Reliability**
- "Green" Device (Note 4)**

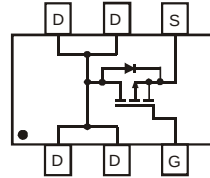
Mechanical Data

- Case: SOT-26
- Case Material – Molded Plastic. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish - Matte Tin Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 2
- Ordering Information: See page 2
- Weight: 0.008 grams (approximate)

SOT-26



TOP VIEW


TOP VIEW
Internal Schematic

Maximum Ratings @ $T_A = 25^\circ C$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current (Note 1) Continuous	I_D	$T_A = 25^\circ C$ -3.4	A
		$T_A = 70^\circ C$ -2.7	
Pulsed Drain Current (Note 2)	I_{DM}	-12	A
Body-Diode Continuous Current (Note 1)	I_S	2.0	A

Thermal Characteristics

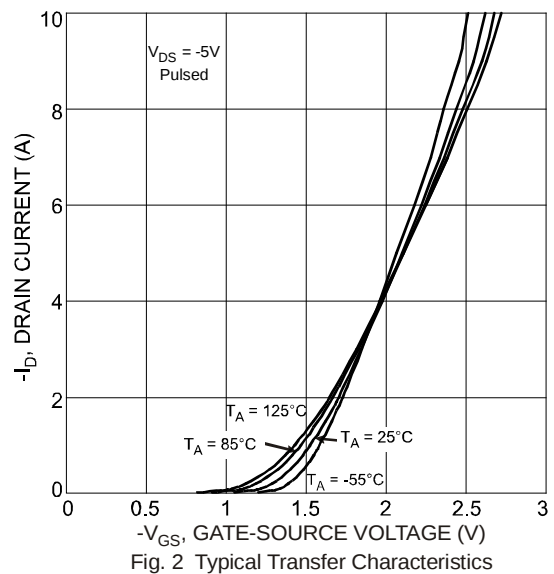
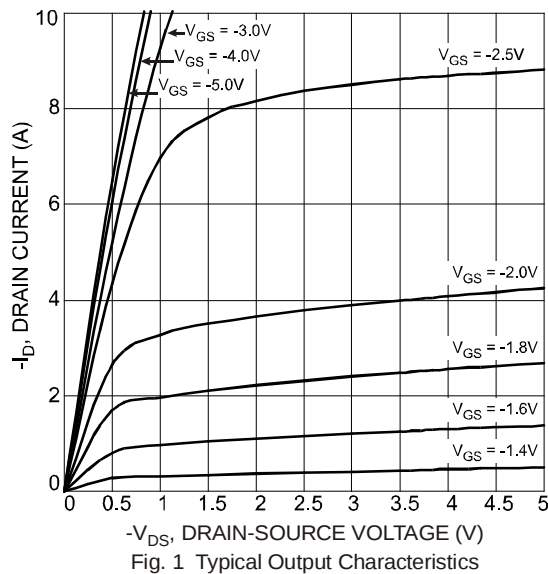
Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	P_D	1.25	W
Thermal Resistance, Junction to Ambient (Note 1); Steady-State	$R_{\theta JA}$	100	$^\circ C/W$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ C$

- Notes:
- Device mounted on 1"x1", FR-4 PC board with 2 oz. Copper and test pulse width $t \leq 10s$.
 - Repetitive Rating, pulse width limited by junction temperature.
 - No purposefully added lead.
 - Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	I _D = -250μA, V _{GS} = 0V
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	μA	V _{DS} = -20V, V _{GS} = 0V
Gate-Body Leakage Current	I _{GSS}	—	—	±100	nA	V _{DS} = 0V, V _{GS} = ±12V
Gate Threshold Voltage	V _{GS(th)}	-0.6	—	-1.25	V	V _{DS} = V _{GS} , I _D = -250μA
On State Drain Current (Note 5)	I _{D(ON)}	-15	—	—	A	V _{GS} = -4.5V, V _{DS} = -5V
Static Drain-Source On-Resistance (Note 5)	R _{DS(ON)}	—	51	80	mΩ	V _{GS} = -4.5V, I _D = -4.5A
			82	110		V _{GS} = -2.7V, I _D = -3.8A
			94	130		V _{GS} = -2.5V, I _D = -3.7A
Forward Transconductance (Note 5)	g _{FS}	—	6.3	—	S	V _{DS} = -10V, I _D = -4.5A
Diode Forward Voltage (Note 5)	V _{SD}	—	0.79	-1.26	V	I _S = -1.7A, V _{GS} = 0V
Maximum Body-Diode Continuous Current (Note 1)	I _S	—	—	1.7	A	—
DYNAMIC PARAMETERS (Note 6)						
Total Gate Charge	Q _g	—	7.3	—	nC	V _{GS} = -4.5V, V _{DS} = -10V, I _D = 4.5A
Gate-Source Charge	Q _{gs}	—	2.0	—	nC	V _{GS} = -4.5V, V _{DS} = -10V, I _D = 4.5A
Gate-Drain Charge	Q _{gd}	—	1.9	—	nC	V _{GS} = -4.5V, V _{DS} = -10V, I _D = 4.5A
Turn-On Delay Time	t _{D(on)}	—	12	—	ns	V _{DS} = -10V, V _{GS} = -4.5V, R _L = 10Ω, R _G = 6Ω
Turn-On Rise Time	t _r	—	20	—	ns	
Turn-Off Delay Time	t _{D(off)}	—	38	—	ns	
Turn-Off Fall Time	t _f	—	41	—	ns	V _{DS} = -16V, V _{GS} = 0V f = 1.0MHz
Input Capacitance	C _{iss}	—	443	—	pF	
Output Capacitance	C _{oss}	—	125	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	98	—	pF	

Notes: 5. Test pulse width t = 300μs.
6. Guaranteed by design. Not subject to production testing.



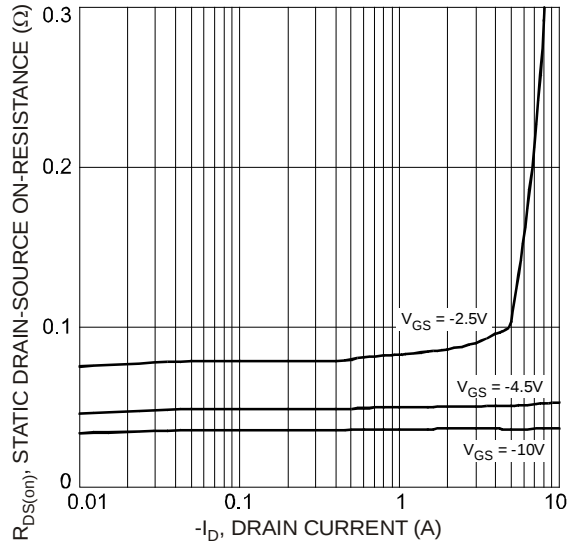


Fig. 3 On-Resistance vs. Drain Current and Gate Voltage

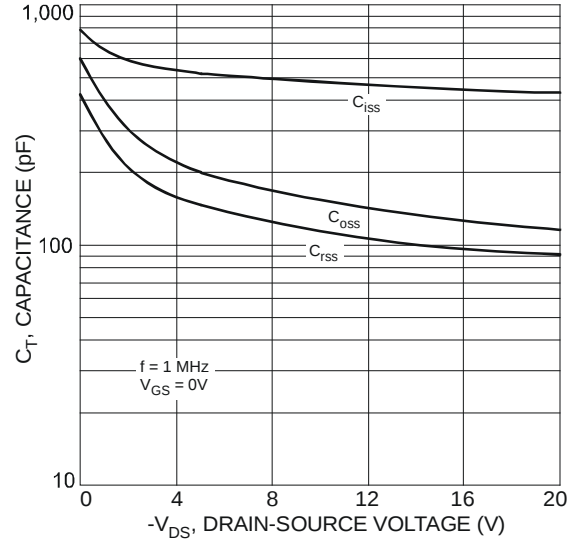


Fig. 4 Typical Total Capacitance

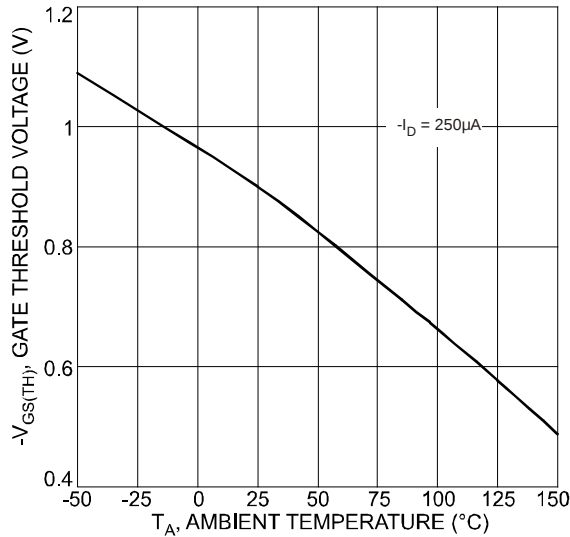


Fig. 5 Gate Threshold Voltage vs. Ambient Temperature

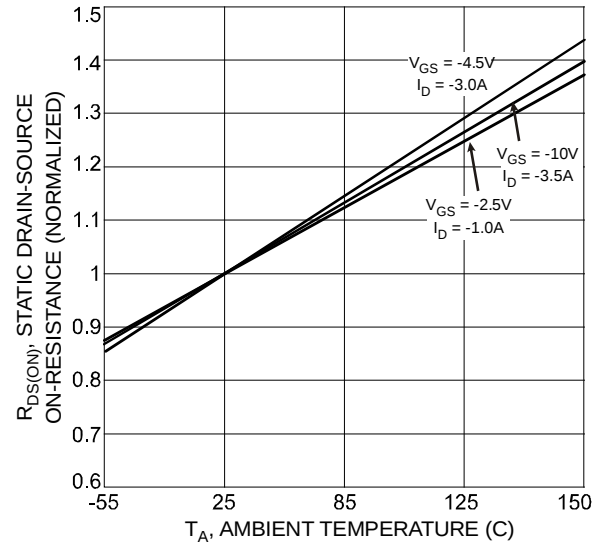


Fig. 6 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

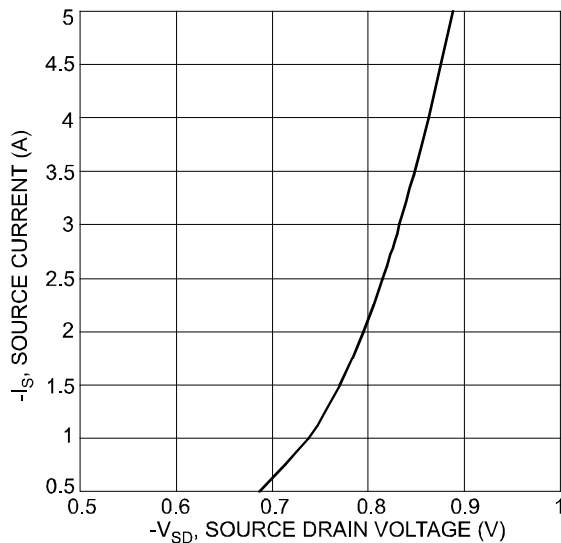


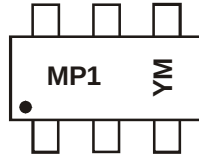
Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

Ordering Information (Note 7)

Part Number	Case	Packaging
DMP2130LDM-7	SOT-26	3000/Tape & Reel

Notes: 7. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



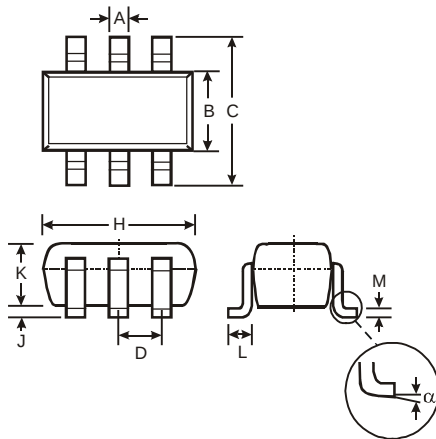
MP1 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year ex: U = 2007
 M = Month ex: 9 = September

Date Code Key

Year	2007		2008		2009		2010		2011		2012	
Code	U		V		W		X		Y		Z	

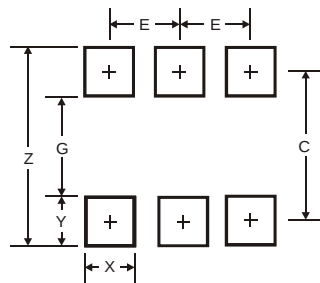
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Package Outline Dimensions



SOT-26			
Dim	Min	Max	Typ
A	0.35	0.50	0.38
B	1.50	1.70	1.60
C	2.70	3.00	2.80
D	—	—	0.95
H	2.90	3.10	3.00
J	0.013	0.10	0.05
K	1.00	1.30	1.10
L	0.35	0.55	0.40
M	0.10	0.20	0.15
α	0°	8°	—
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.20
G	1.60
X	0.55
Y	0.80
C	2.40
E	0.95

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Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9